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PZT3906

SMALL SIGNAL PNP TRANSISTOR

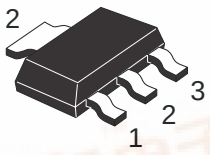
PRELIMINARY DATA

Type	Marking
PZT3906	3906

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS PZT3904

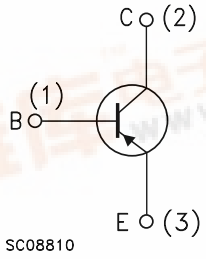
APPLICATIONS

- WELL SUITABLE FOR SMD MOTHER BOARD ASSEMBLY
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



SOT-223

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	-60	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	-40	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	-6	V
I_C	Collector Current	-200	mA
P_{tot}	Total Dissipation at T_C = 25 °C	1	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

$R_{thj\text{-}amb}$ •	Thermal Resistance Junction-Ambient	Max	125	°C/W

• Device mounted on a PCB of 1 cm^2

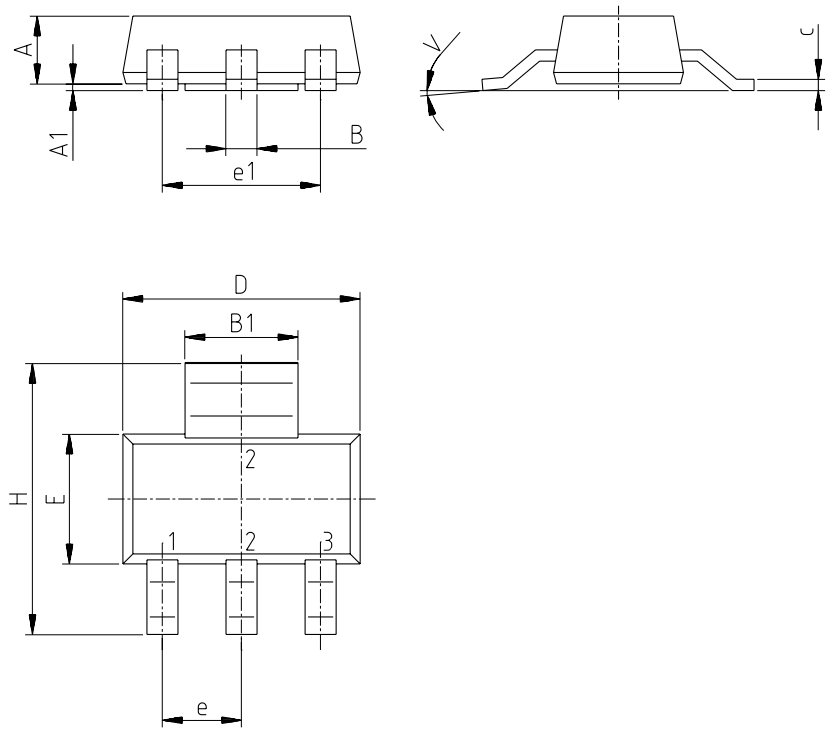
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX}	Collector Cut-off Current (V_{BE} = 3 V)	V_{CE} = -30 V			-50	nA
I_{BEX}	Collector Cut-off Current (V_{BE} = 3 V)	V_{CE} = -30 V			-50	nA
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage (I_B = 0)	I_C = -1 mA	-40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I_E = 0)	I_C = -10 µA	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = -10 µA	-6			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = -10 mA I_B = -1 mA I_C = -50 mA I_B = -5 mA			-0.25 -0.4	V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = -10 mA I_B = -1 mA I_C = -50 mA I_B = -5 mA	 -0.65		-0.85 -0.95	V V
h_{FE}*	DC Current Gain	I_C = -0.1 mA V_{CE} = -1 V I_C = -1 mA V_{CE} = -1 V I_C = -10 mA V_{CE} = -1 V I_C = -50 mA V_{CE} = -1 V I_C = -100 mA V_{CE} = -1 V	60 80 100 60 30		 300	
f_T	Transition Frequency	I_C = -10mA V_{CE} = -20 V f = 100MHz	250			MHz
NF	Noise Figure	V_{CE} = -5 V I_C = -0.1 mA f = 10 Hz to 15.7 KHz R_G = 1 KΩ		4		dB
C_{CBO}	Collector-Base Capacitance	I_E = 0 V_{CB} = -5 V f = 100 KHz		6		pF
C_{EBO}	Emitter-Base Capacitance	I_C = 0 V_{EB} = -0.5 V f = 100 KHz		25		pF
t_d	Delay Time	I_C = -10 mA I_B = -1 mA V_{CC} = -3V			35	ns
t_r	Rise Time				35	ns
t_s	Storage Time	I_C = -10 mA I_{B1} = $-I_{B2}$ = -1 mA V_{CC} = -3V			225	ns
t_f	Fall Time				72	ns

∗ Pulsed: Pulse duration = 300 µs, duty cycle ≤ 2 %

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10^o			10^o
A1		0.02				



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